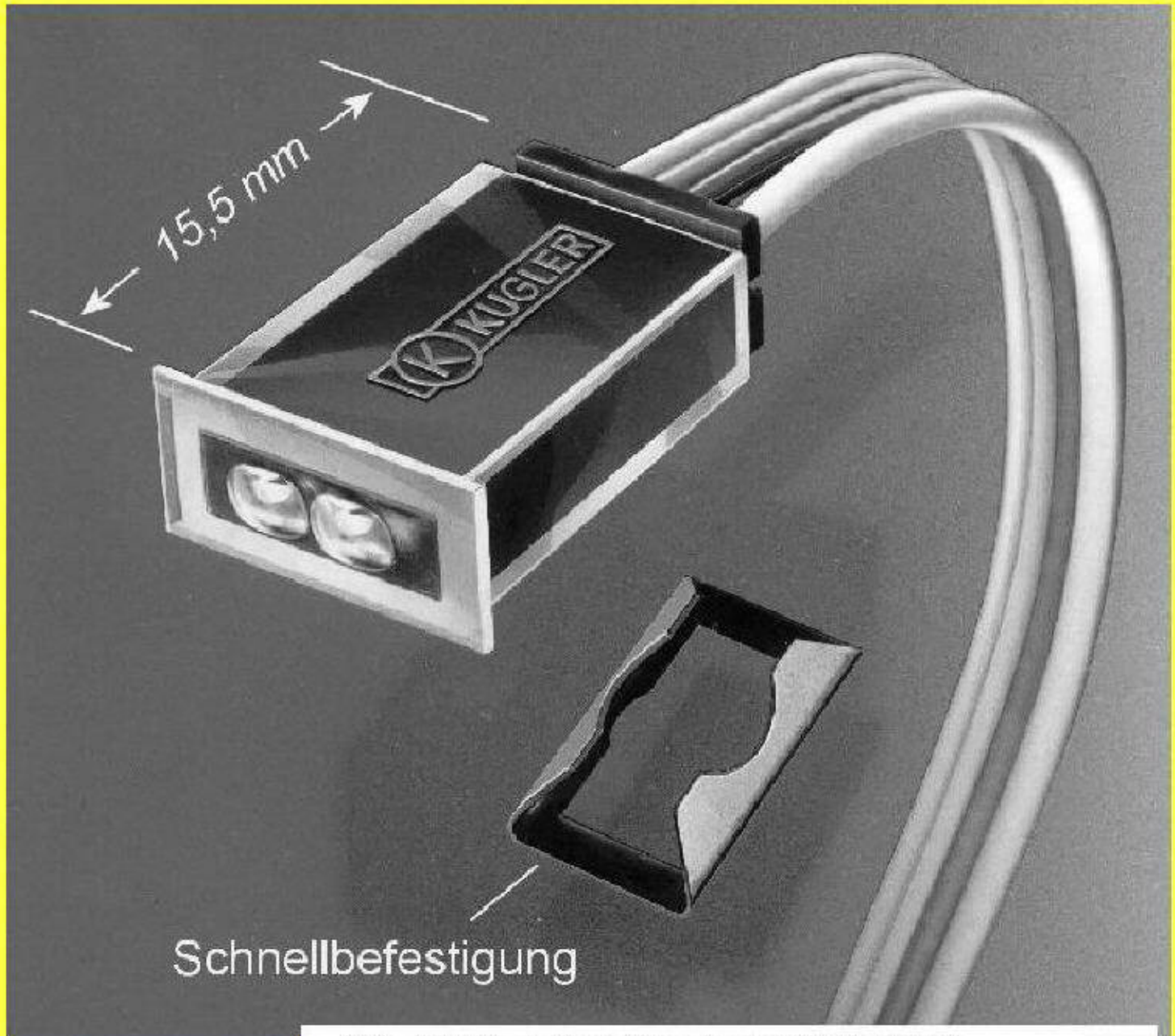


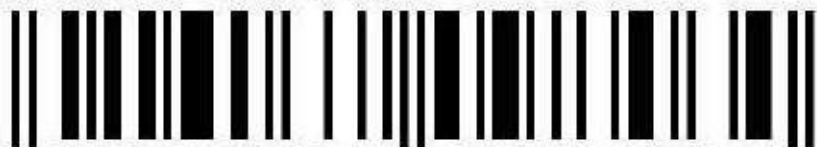
IR-Miniatur-Reflexlichttaster MRL601

zur Abtastung von Reflektoren im Bereich
von 1 - 30 mm, mit Schnellbefestigung



IR-Reflexlichttaster MRL601

Best.Nr. 182230



4 016138 098464

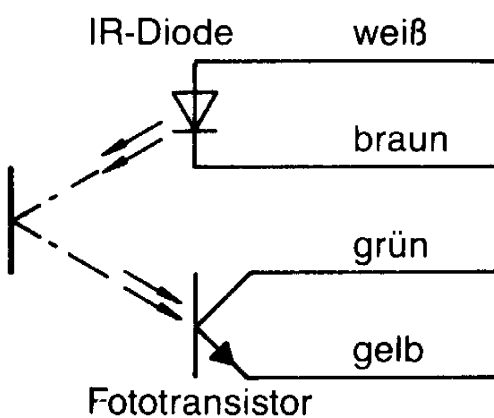
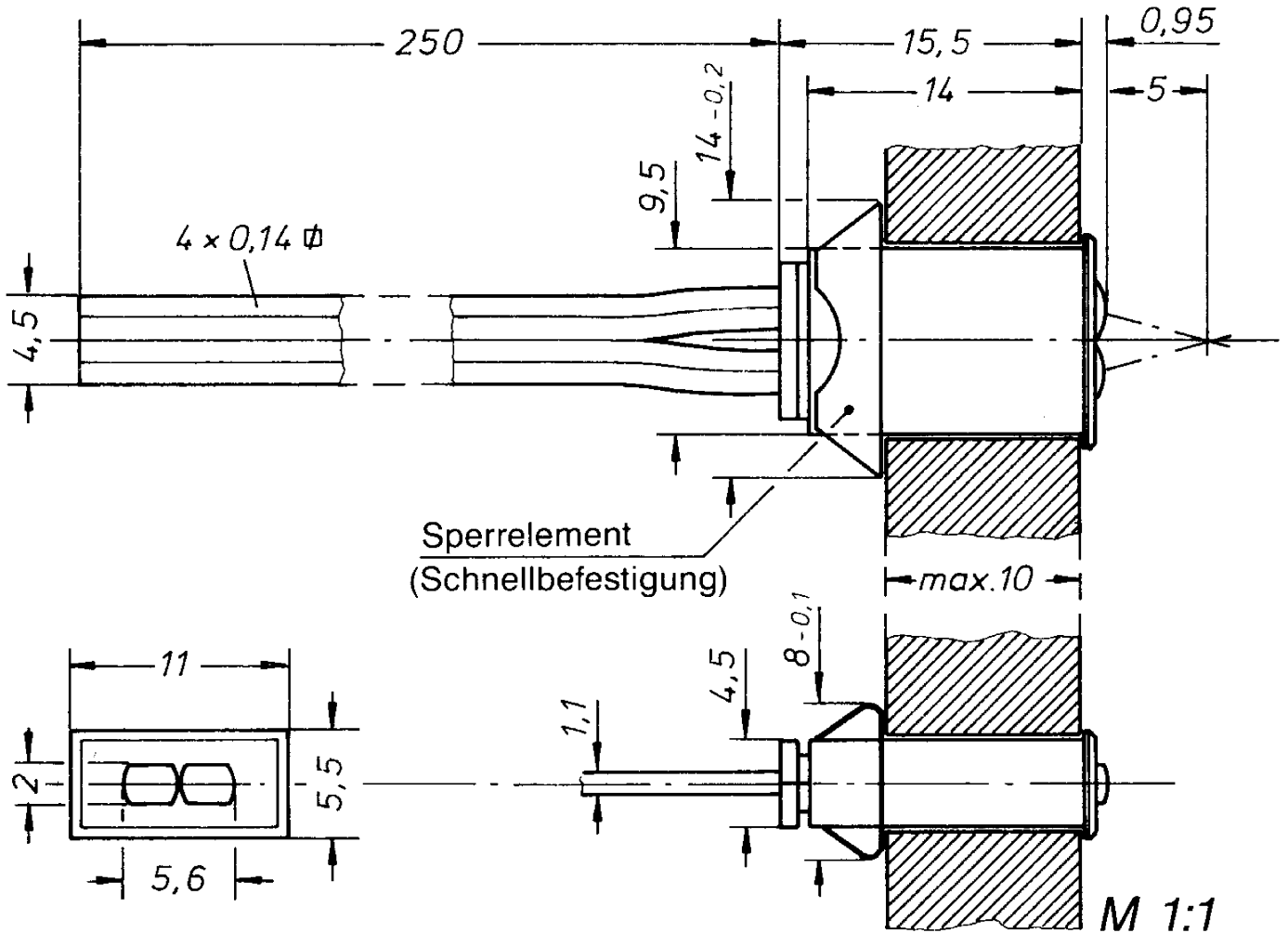
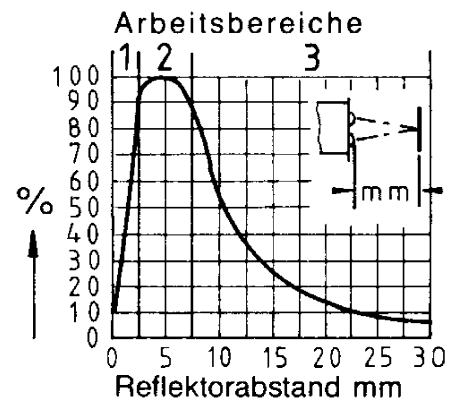
96220226

MRL 601

Relativer
Fotostrom
in Abhängigkeit vom
Reflektorabstand:

Arbeitsbereich:

- 1 möglichst meiden
- 2 Abtastung von Markierungen möglich
- 3 nur für die Abtastung großflächiger, guter Reflektoren



Grenzdaten:
Sperrspannung
Durchlaßstrom
Durchlaßspannung
Verlustleistung

Kollektor-Emittersp.
Kollektorstrom
Verlustleistung

IR-Diode

U_R	5	V
I_F	60	mA
U_F	1,25	V ($I_F = 50$ mA)
P_{tot}	85	mW ($T_U = 25^\circ\text{C}$)

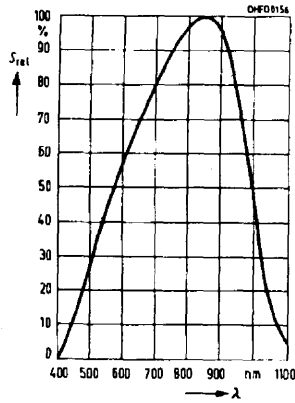
Fototransistor

U_{CE}	32	V
I_C	50	mA
P_{tot}	100	mW ($T_U = 25^\circ\text{C}$)

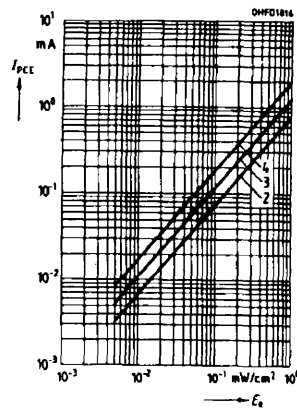
SILICON NPN PHOTOTRANSISTOR

MRL 601

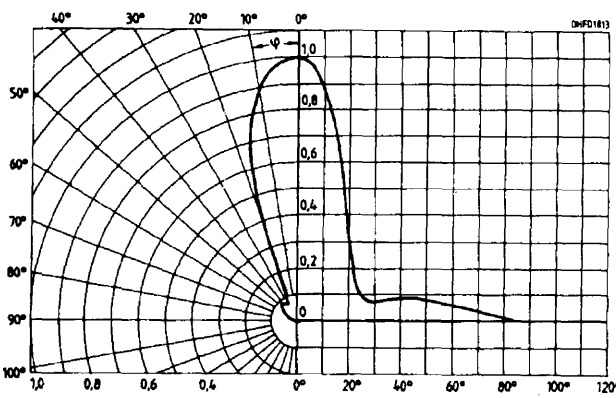
Relative spectral sensitivity
 $S_{REL}=f(\lambda)$



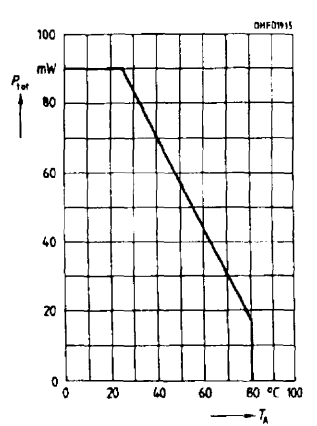
Photocurrent $I_{PCE}=f(E_e)$



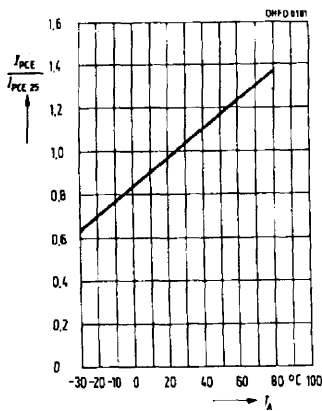
Directional characteristic
 $S_{REL}=f(\varphi)$



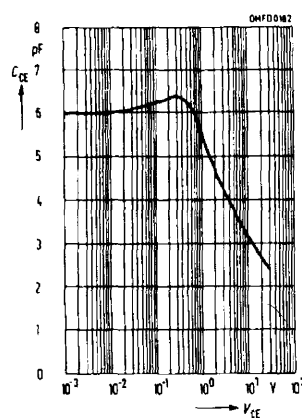
Total power dissipation
 $P_{TOT}=f(T_A)$



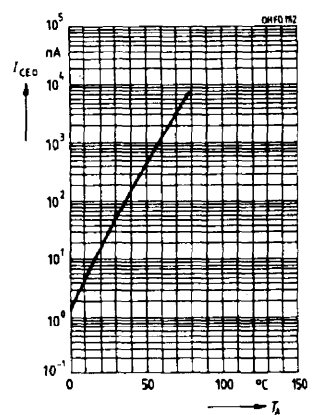
Photocurrent $I_{PCE}/I_{PCE25}=f(T_A)$,
 $V_{CE}=5\text{ V}$



Collector emitter capacitance
 $C_{CE}=f(V_{CE})$, $f=1\text{ MHz}$, $E=0$



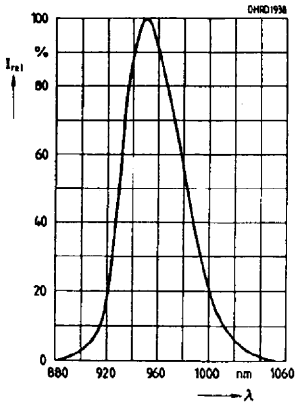
Dark current
 $I_{CEO}=f(T_A)$, $V_{CE}=25\text{ V}$, $E=0$



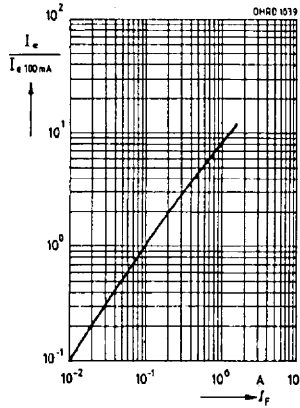
INFRARED EMITTER DIODES

MRL 601

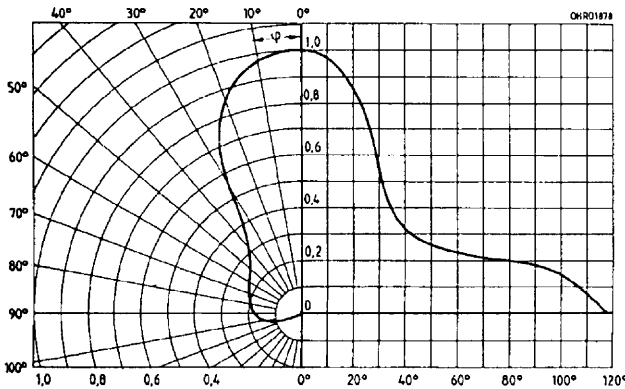
Relative spectral emission $I_{REL}=f(\lambda)$



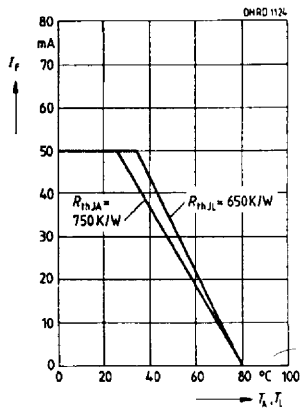
Radiant Intensity $I_E/I_{E50mA}=f(I_F)$
Single pulse, $\tau=20 \mu s$



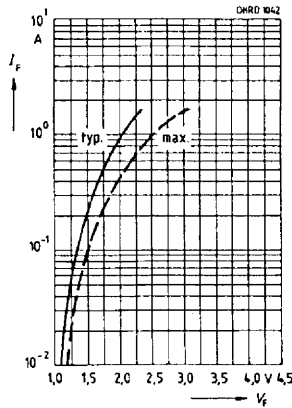
Radiation characteristic $I_{REL}=f(\varphi)$



Maximum permissible forward current $I_F=f(T_A)$



Forward current $I_F=f(V_F)$



Permissible pulse handling capability $I_F=f(\tau)$, $T_C=25^\circ C$
duty cycle D =Parameter

